

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,849,901 B2
DATED : February 1, 2005
INVENTOR(S) : Falster

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

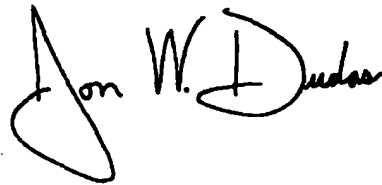
Title page,

Item [54], Title, should read:

-- **SILICON-ON-INSULATOR STRUCTURE HAVING A DEVICE LAYER
WHICH IS VACANCY DOMINATED AND SUBSTANTIALLY FREE OF
AGGLOMERATED VACANCY-TYPE DEFECTS** --.

Signed and Sealed this

Thirteenth Day of December, 2005

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a cursive "Dudas".

JON W. DUDAS
Director of the United States Patent and Trademark Office